2SB1734 Silicon PNP epitaxial planar type

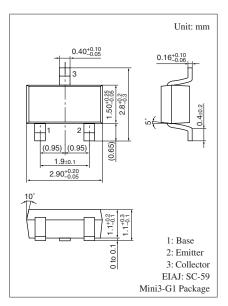
For general amplification Complementary to 2SD2706

Features

- \bullet High forward current transfer ratio $h_{F\!E}$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V _{CBO}	-50	V					
Collector-emitter voltage (Base open)	V _{CEO}	-50	V					
Emitter-base voltage (Collector open)	V _{EBO}	-5	V					
Collector current	I _C	-200	mA					
Peak collector current	I _{CP}	-400	mA					
Collector power dissipation	P _C	200	mW					
Junction temperature	Tj	150	°C					
Storage temperature	T _{stg}	-55 to +150	°C					





Marking Symbol: AF

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = -10 \ \mu A, \ I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$	85		500	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$			-300	mV
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3		pF
(Common base, input open circuited)						

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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